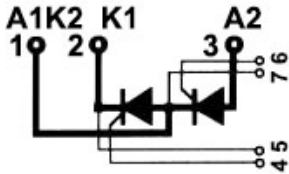


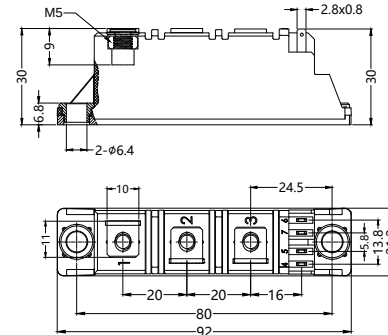
STT90GK20B

Thyristor-Thyristor Modules



Type	V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V
STT90GK08B	900	800
STT90GK12B	1300	1200
STT90GK14B	1500	1400
STT90GK16B	1700	1600
STT90GK18B	1900	1800
STT90GK20B	2100	2000

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
I_{TRMS}, I_{FRMS} I_{TAVM}, I_{FAVM}	$T_V = T_{VJM}$ $T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	140 90	A
I_{TSM}, I_{FSM}	$T_V = 45^\circ\text{C}$ $V_R = 0$ $t = 10\text{ms (50Hz), sine}$ $t = 8.3\text{ms (60Hz), sine}$	1700 1800	A
	$T_V = T_{VJM}$ $V_R = 0$ $t = 10\text{ms (50Hz), sine}$ $t = 8.3\text{ms (60Hz), sine}$	1540 1640	
$\int i^2 dt$	$T_V = 45^\circ\text{C}$ $V_R = 0$ $t = 10\text{ms (50Hz), sine}$ $t = 8.3\text{ms (60Hz), sine}$	14450 13500	A^2s
	$T_V = T_{VJM}$ $V_R = 0$ $t = 10\text{ms (50Hz), sine}$ $t = 8.3\text{ms (60Hz), sine}$	11850 11300	
$(di/dt)_{cr}$	$T_V = T_{VJM}$ $f = 50\text{Hz}, t_p = 200\mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.45\text{A}$ $di_G/dt = 0.45\text{A}/\mu\text{s}$ repetitive, $I_T = 250\text{A}$	150	A/ μs
	non repetitive, $I_T = I_{TAVM}$	500	
$(dv/dt)_{cr}$	$T_V = T_{VJM}; V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	V/ μs
P_{GM}	$T_V = T_{VJM}$ $t_p = 30\mu\text{s}$	10	W
	$I_T = I_{TAVM}$ $t_p = 300\mu\text{s}$	5	
P_{GAV}		0.5	W
V_{RGM}		10	V
T_V T_{VJM} T_{stg}		-40...+125 125 -40...+125	$^\circ\text{C}$
V_{ISOL}	50/60Hz, RMS $I_{ISOL} \leq 1\text{mA}$ $t = 1\text{min}$ $t = 1\text{s}$	3000 3600	V~
M_d	Mounting torque (M5) Terminal connection torque (M5)	2.5-4.0/22-35 2.5-4.0/22-35	Nm/lb.in.
Weight	Typical	110	g

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Thyristor-Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
I_{RRM}, I_{DRM}	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
V_{TM}	$I_{TM}=270A; T_{VJ}=25^{\circ}C$	1.74	V
V_{TO}	For power-loss calculations only ($T_{VJ}=125^{\circ}C$)	0.85	V
r_T		3.2	m Ω
V_{GT}	$V_D=6V$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
I_{GT}	$V_D=6V$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	150 200	mA
V_{GD}	$T_{VJ}=T_{VJM}$ $V_D=2/3V_{DRM}$	0.2	V
I_{GD}		10	mA
I_L	$T_{VJ}=25^{\circ}C; t_p=10\mu s; V_D=6V I_G=0.45A; di_G/dt=0.45A/\mu s$	450	mA
I_H	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	200	mA
t_{gd}	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM} I_G=0.45A; di_G/dt=0.45A/\mu s$	2	μs
t_q	$T_{VJ}=T_{VJM}; I_T=150A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$ typ.	185	μs
Q_s	$T_{VJ}=T_{VJM}; I_T, I_F=50A; -di/dt=6A/\mu s$	170	μC
I_{RM}		45	A
R_{thJC}	per thyristor/diode; DC current per module	0.3 0.15	K/W
R_{thJK}	per thyristor/diode; DC current per module	0.5 0.25	K/W
ds	Creeping distance on surface	12.7	mm
da	Strike distance through air	9.6	mm
a	Maximum allowable acceleration	50	m/s ²

FEATURES

- * International standard package
- * Copper base plate
- * Glass passivated chips
- * Isolation voltage 3600 V~
- * UL file NO.E310749
- * RoHS compliant

APPLICATIONS

- * DC motor control
- * Softstart AC motor controller
- * Light, heat and temperature control

ADVANTAGES

- * Space and weight savings
- * Simple mounting with two screws
- * Improved temperature and power cycling
- * Reduced protection circuits



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Thyristor-Thyristor Modules

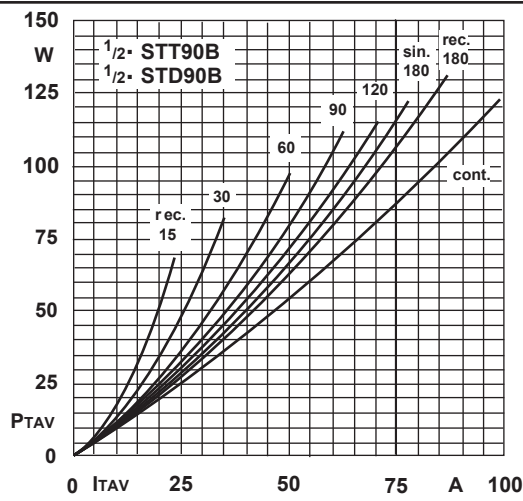


Fig.1L Power dissipation per thyristor vs. on-state current

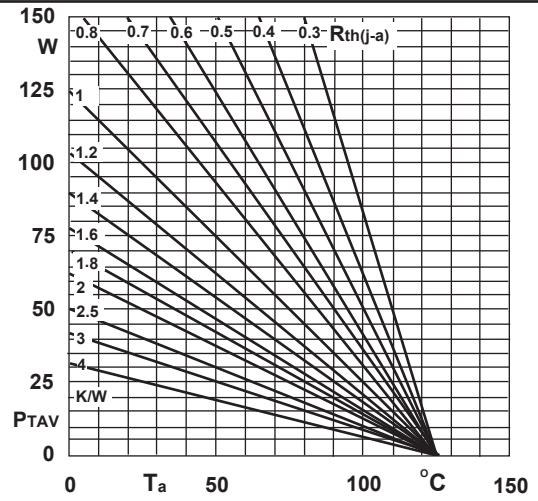


Fig.1R Power dissipation per thyristor vs. ambient temp

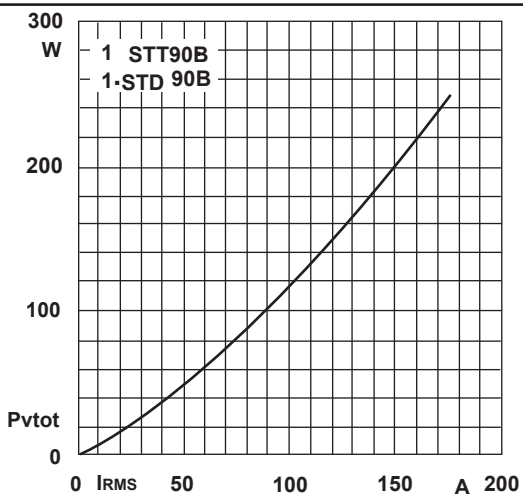


Fig.2L Power dissipation per module vs. rms current

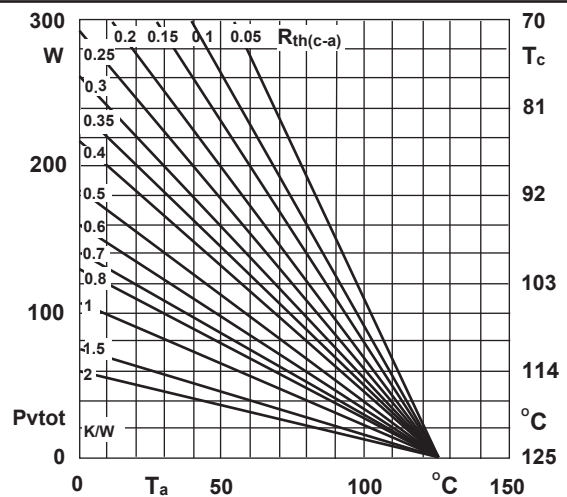


Fig.2R Power dissipation per module vs. case temp

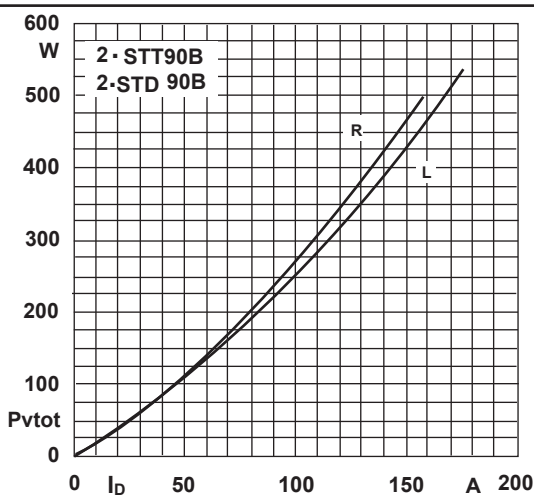


Fig.3L Power dissipation of two modules vs. direct current

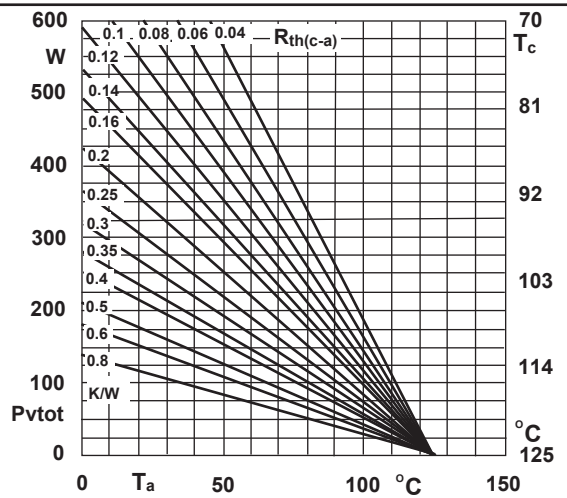


Fig.3R Power dissipation of two modules vs. case temp

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Thyristor-Thyristor Modules

